Kozo Fujiwara

List of Publications by Year in Descending Order

174 papers	2,734 citations	27 h-index	43 g-index
180 ext. papers	2,969 ext. citations	3.1 avg, IF	4.74 L-index

#	Paper	IF	Citations
174	Twin boundary formation at a grain-boundary groove during the directional solidification of InSb. *Journal of Crystal Growth*, **2022**, 577, 126403	1.6	
173	Dynamics at crystal/melt interface during solidification of multicrystalline silicon. *High Temperature Materials and Processes*, **2022**, 41, 31-47	0.9	0
172	Facet formation during the solidification of pure antimony. *Journal of Crystal Growth*, **2022**, 586, 126633	1.6	
171	Dendritic Growth in Si1−xGex Melts. *Crystals*, **2021**, 11, 761	2.3	
170	Segregation mechanism of arsenic dopants at grain boundaries in silicon. *Science and Technology of Advanced Materials Methods*, **2021**, 1, 169-180		2
169	Seeded Growth of Type-II Na24Si136 Clathrate Single Crystals. *Crystals*, **2021**, 11, 808	2.3	1
168	In situ observation of multiple parallel (1 1 1) twin boundary formation from step-like grain boundary during Si solidification. *Applied Physics Express*, **2020**, 13, 105501	2.4	2
167	In situ observation of the solidification interface and grain boundary development of two silicon seeds with simultaneous measurement of temperature profile and undercooling. *Journal of Crystal Growth*, **2020**, 532, 125428	1.6	3
166	Effect of twin boundary formation on the growth rate of the GaSb{111} plane. *Acta Materialia*, **2020**, 185, 453-460	8.4	2
165	Crystallization and re-melting of Si1-xGex alloy semiconductor during rapid cooling. *Journal of Alloys and Compounds*, **2019**, 798, 493-499	5.7	5
164	The in situ observation of faceted dendrite growth during the directional solidification of GaSb. *Scripta Materialia*, **2019**, 168, 56-60	5.6	5
163	A {112}Σ3 grain boundary generated from the decomposition of a Σ9 grain boundary in multicrystalline silicon during directional solidification. *Scripta Materialia*, **2019**, 167, 46-50	5.6	5
162	The effect of grain boundaries on instability at the crystal/melt interface during the unidirectional growth of Si. *Materialia*, **2019**, 7, 100386	3.2	5
161	Effect of misorientation angle of grain boundary on the interaction with Σ3 boundary at crystal/melt interface of multicrystalline silicon. *Materialia*, **2019**, 7, 100357	3.2	4
160	Influence of interfacial structure on propagating direction of small-angle grain boundaries during directional solidification of multicrystalline silicon. *Scripta Materialia*, **2019**, 172, 105-109	5.6	3
159	Growth of Multicrystalline Silicon for Solar Cells: Dendritic Cast Method **2019**, 1-22		
158	Growth of Multicrystalline Silicon for Solar Cells: Dendritic Cast Method **2019**, 193-214		

157	In situ observation of interaction between grain boundaries during directional solidification of Si. *Scripta Materialia*, **2018**, 148, 37-41	5.6	11
156	Application of weighted Voronoi diagrams to analyze nucleation sites of multicrystalline silicon ingots. *Journal of Crystal Growth*, **2018**, 499, 62-66	1.6	4
155	In situ observation of grain-boundary development from a facet-facet groove during solidification of silicon. *Acta Materialia*, **2018**, 153, 186-192	8.4	11
154	In situ observation of grain boundary groove at the crystal/melt interface in Cu. *Scripta Materialia*, **2018**, 146, 169-172	5.6	6
153	Crystal Growth Conditions of Types I and II Na□Si Clathrates by Evaporation of Na from a Na□Si□Sn Solution. *Crystal Growth and Design*, **2018**, 18, 351-355	3.5	5
152	In-situ studies of multicrystalline silicon nucleation and growth on □and □Si3N4 coated substrates. *Journal of Crystal Growth*, **2018**, 482, 75-84	1.6	2
151	Investigation of Si Dendrites by Electron-Beam-Induced Current. *Crystals*, **2018**, 8, 317	2.3	1
150	In-situ observation of instability of a crystal□melt interface during the directional growth of pure antimony. *AIP Advances*, **2018**, 8, 075121	1.5	5
149	Origin of small-angle grain boundaries during directional solidification in multicrystalline silicon. *Materialia*, **2018**, 3, 347-352	3.2	4
148	In situ observation of twin boundary formation at grain-boundary groove during directional solidification of Si. *Scripta Materialia*, **2017**, 133, 65-69	5.6	19
147	Impact of local atomic stress on oxygen segregation at tilt boundaries in silicon. *Applied Physics Letters*, **2017**, 110, 062105	3.4	15
146	Effect of point defects on Curie temperature of lithium niobate. *Journal of the American Ceramic Society*, **2017**, 100, 1118-1124	3.8	3
145	Effect of an External Electric Field on the Kinetics of Dislocation-Free Growth of Tetragonal Hen Egg White Lysozyme Crystals. *Crystals*, **2017**, 7, 170	2.3	8
144	Growth of Multicrystalline Silicon for Solar Cells: Dendritic Cast Method **2017**, 1-22		
143	Effect of grain boundary grooves at the crystal/melt interface on impurity accumulation during the unidirectional growth of multicrystalline silicon. *Scripta Materialia*, **2016**, 117, 73-76	5.6	12
142	Technique for High-Quality Protein Crystal Growth by Control of Subgrain Formation under an External Electric Field. *Crystals*, **2016**, 6, 95	2.3	9
141	Orientation-dependent impurity partitioning of colloidal crystals. *Journal of Crystal Growth*, **2016**, 439, 13-18	1.6	1
140	Effect of Solid□iquid Interface Morphology on Grain Boundary Segregation during Colloidal Polycrystallization. *Crystal Growth and Design*, **2016**, 16, 2765-2770	3.5	4

139	Liquid immiscibility in a CTGS (Ca3TaGa3Si2O14) melt. *Journal of Crystal Growth*, **2016**, 454, 82-86	1.6	5
138	Segregation of Ge in B and Ge codoped Czochralski-Si crystal growth. *Journal of Alloys and Compounds*, **2015**, 639, 588-592	5.7	1
137	The solid-solution region for the langasite-type Ca3TaGa3Si2O14 crystal as determined by a lever rule. *Journal of Crystal Growth*, **2015**, 415, 111-117	1.6	2
136	Grain Boundary Segregation of Impurities During Polycrystalline Colloidal Crystallization. *Crystal Growth and Design*, **2015**, 15, 5685-5692	3.5	7
135	Investigation of defect structure of impurity-doped lithium niobate by combining thermodynamic constraints with lattice constant variations. *Journal of Applied Physics*, **2015**, 117, 014102	2.5	5
134	Grain Growth in the Melt **2015**, 723-748		3
133	Liquinert quartz crucible for the growth of multicrystalline Si ingots. *Energy Science and Engineering* , **2015**, 3, 419-422	3.4	11
132	Three-dimensional evaluation of gettering ability for oxygen atoms at small-angle tilt boundaries in Czochralski-grown silicon crystals. *Applied Physics Letters*, **2015**, 106, 251603	3.4	13
131	Crystallization of high-quality protein crystals using an external electric field. *Journal of Applied Crystallography*, **2015**, 48, 1507-1513	3.8	18
130	Partitioning of ionic species during growth of impurity-doped lithium niobate by electric current injection. *Journal of Crystal Growth*, **2014**, 406, 78-84	1.6	6
129	Crystal growth under external electric fields **2014**,		2
128	Instability of crystal/melt interface including twin boundaries of silicon. *Applied Physics Letters*, **2014**, 104, 182110	3.4	11
127	Crystal growth and equilibrium crystal shapes of silicon in the melt. *Progress in Photovoltaics: Research and Applications*, **2014**, 22, 574-580	6.8	12
126	Growth of congruent-melting lithium tantalate crystal with stoichiometric structure by MgO doping. *Journal of Crystal Growth*, **2013**, 383, 63-66	1.6	7
125	Grown-in microdefects and photovoltaic characteristics of heavily Ge co-doped Czochralski-grown p-type silicon crystals. *Scripta Materialia*, **2013**, 69, 686-689	5.6	3
124	Germanium-doped Czochralski silicon: a novel material for solar cells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1746-1749		2
123	Improvement of crystal quality for tetragonal hen egg white lysozyme crystals under application of an external alternating current electric field. *Journal of Applied Crystallography*, **2013**, 46, 25-29	3.8	21
122	Impurity partitioning during colloidal crystallization. *Journal of Physical Chemistry B*, **2013**, 117, 5289-95	3.4	18

121	The effect of grain boundary characteristics on the morphology of the crystal/melt interface of multicrystalline silicon. *Scripta Materialia*, **2013**, 69, 266-269	5.6	27
120	Evaluation of crystalline silicon solar cells by current-modulating four-point-probe method. *Applied Physics Letters*, **2013**, 103, 043903	3.4	
119	Fabrication of Quasi-Phase-Matching Structure during Paraelectric Borate Crystal Growth. *Applied Physics Express*, **2013**, 6, 015501	2.4	3
118	Control of Gibbs free energy relationship between hen egg white lysozyme polymorphs under application of an external alternating current electric field. *Journal of Applied Crystallography*, **2012**, 45, 207-212	3.8	5
117	The critical growth velocity for planar-to-faceted interfaces transformation in SiGe crystals. *Applied Physics Letters*, **2012**, 100, 141601	3.4	11
116	Nucleation rate enhancement of porcine insulin by application of an external AC electric field. *Journal of Crystal Growth*, **2012**, 352, 155-157	1.6	19
115	Growth velocity and grain size of multicrystalline solar cell silicon. *Journal of Crystal Growth*, **2012**, 356, 17-21	1.6	9
114	Formation mechanism of cellular structures during unidirectional growth of binary semiconductor Si-rich SiGe materials. *Applied Physics Letters*, **2012**, 100, 021903	3.4	21
113	Crystal and faceted dendrite growth of silicon near (1 0 0). *Acta Materialia*, **2012**, 60, 3259-3267	8.4	9
112	Crystal Growth Behaviors of Silicon during Melt Growth Processes. *International Journal of Photoenergy*, **2012**, 2012, 1-16	2.1	23
111	Boron-oxygen defect in Czochralski-silicon co-doped with gallium and boron. *Applied Physics Letters* , **2012**, 100, 042110	3.4	42
110	Effect of silicon/crucible interfacial energy on orientation of multicrystalline silicon ingot in unidirectional growth. *Journal of Applied Physics*, **2012**, 112, 113521	2.5	9
109	The impact of Ge codoping on the enhancement of photovoltaic characteristics of B-doped Czochralski grown Si crystal. *Journal of Applied Physics*, **2012**, 111, 043707	2.5	10
108	Formation mechanism of twin boundaries in lithium tetraborate. *Journal of Crystal Growth*, **2011**, 331, 78-82	1.6	2
107	Generation mechanism of dislocations and their clusters in multicrystalline silicon during two-dimensional growth. *Journal of Applied Physics*, **2011**, 110, 083530	2.5	18
106	Formation mechanism of twin boundaries during crystal growth of silicon. *Scripta Materialia*, **2011**, 65, 556-559	5.6	21
105	Dependence of Si-Faceted Dendrite Growth Orientation on Twin Spacing and Undercooling. *Crystal Growth and Design*, **2011**, 11, 1402-1410	3.5	10
104	Control of effect on the nucleation rate for hen egg white lysozyme crystals under application of an external ac electric field. *Langmuir*, **2011**, 27, 8333-8	4	21

103	Morphological transformation of a crystal–melt interface during unidirectional growth of silicon. *Acta Materialia*, **2011**, 59, 4700-4708	8.4	38
102	Plastically deformed Si-crystal wafers for neutron-monochromator elements. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2011**, 635, 137-140	1.2	4
101	Arrangement of dendrite crystals grown along the bottom of Si ingots using the dendritic casting method by controlling thermal conductivity under crucibles. *Journal of Crystal Growth*, **2011**, 319, 13-18	1.6	41
100	The impact of Ge codoping on grown-in O precipitates in Ga-doped Czochralski-silicon. *Journal of Crystal Growth*, **2011**, 321, 24-28	1.6	1
99	Implementation of faceted dendrite growth on floating cast method to realize high-quality multicrsytalline Si ingot for solar cells. *Journal of Applied Physics*, **2011**, 109, 083527	2.5	18
98	Dependence of Si faceted dendrite growth velocity on undercooling. *Applied Physics Letters*, **2011**, 98, 012113	3.4	18
97	Growth mechanism of the Si <110> faceted dendrite. *Physical Review B*, **2010**, 81,	3.3	22
96	Relationship between grain boundary structures in Si multicrystals and generation of dislocations during crystal growth. *Journal of Applied Physics*, **2010**, 107, 013511	2.5	41
95	Role of the Electric Double Layer in Controlling the Nucleation Rate for Tetragonal Hen Egg White Lysozyme Crystals by Application of an External Electric Field. *Crystal Growth and Design*, **2010**, 10, 2591-2595	3.5	29
94	Effect of twin spacing on the growth velocity of Si faceted dendrites. *Applied Physics Letters*, **2010**, 97, 172104	3.4	17
93	Realization of a High-Performance Point-Focusing Monochromator for X-ray Studies. *Applied Physics Express*, **2010**, 3, 046601	2.4	4
92	Ga segregation during Czochralski-Si crystal growth with Ge codoping. *Journal of Crystal Growth*, **2010**, 312, 2865-2870	1.6	5
91	Effect of various precipitants on the nucleation rate of tetragonal hen egg-white lysozyme crystals in an AC external electric field. *Journal of Crystal Growth*, **2010**, 312, 3503-3508	1.6	11
90	Pattern formation mechanism of a periodically faceted interface during crystallization ofSi. *Journal of Crystal Growth*, **2010**, 312, 3670-3674	1.6	13
89	Formation mechanism of a faceted interface: In situ observation of the Si(100) crystal-melt interface during crystal growth. *Physical Review B*, **2009**, 80,	3.3	43
88	Effects of B and Ge codoping on minority carrier lifetime in Ga-doped Czochralski-silicon. *Journal of Applied Physics*, **2009**, 106, 013721	2.5	14
87	Quantitative analysis of subgrain boundaries in Si multicrystals and their impact on electrical properties and solar cell performance. *Journal of Applied Physics*, **2009**, 105, 044909	2.5	24
86	High minority carrier lifetime in Ga-doped Czochralski-grown silicon by Ge codoping. *Applied Physics Letters*, **2009**, 94, 072102	3.4	9

85	Floating cast method to realize high-quality Si bulk multicrystals for solar cells. *Journal of Crystal Growth*, **2009**, 311, 228-231	1.6	34
84	Systematic studies of Si and Ge hemispherical concave wafers prepared by plastic deformation. *Journal of Crystal Growth*, **2009**, 311, 4587-4592	1.6	5
83	Growth behavior of faceted Si crystals at grain boundary formation. *Journal of Crystal Growth*, **2009**, 312, 19-23	1.6	7
82	Microstructures of Si multicrystals and their impact on minority carrier diffusion length. *Acta Materialia*, **2009**, 57, 3268-3276	8.4	34
81	Control of Nucleation Rate for Tetragonal Hen-Egg White Lysozyme Crystals by Application of an Electric Field with Variable Frequencies. *Crystal Growth and Design*, **2009**, 9, 2420-2424	3.5	44
80	Development of high-resolution and light-weight x-ray optics with deformed silicon wafers **2009**,		2
79	Mechanism of Dendrite Crystal Growth. *Advances in Materials Research*, **2009**, 71-82		1
78	Fundamental Understanding of Subgrain Boundaries. *Advances in Materials Research*, **2009**, 83-95		2
77	Impact of Defect Density in Si Bulk Multicrystals on Gettering Effect of Impurities. *Japanese Journal of Applied Physics*, **2008**, 47, 8790-8792	1.4	11
76	Wave-dispersive x-ray spectrometer for simultaneous acquisition of several characteristic lines based on strongly and accurately shaped Ge crystal. *Review of Scientific Instruments*, **2008**, 79, 033110	1.7	8
75	Growth mechanism of Si-faceted dendrites. *Physical Review Letters*, **2008**, 101, 055503	7.4	61
74	Structural Origin of a Cluster of Bright Spots in Reverse Bias Electroluminescence Image of Solar Cells Based on Si Multicrystals. *Applied Physics Express*, **2008**, 1, 075001	2.4	14
73	Point-focusing monochromator crystal realized by hot plastic deformation of a Ge wafer. *Journal of Applied Crystallography*, **2008**, 41, 798-799	3.8	7
72	Influence of growth temperature and cooling rate on the growth of Si epitaxial layer by dropping-type liquid phase epitaxy from the pure Si melt. *Journal of Crystal Growth*, **2008**, 310, 5248-5251	1.6	2
71	In situ observation of Si faceted dendrite growth from low-degree-of-undercooling melts. *Acta Materialia*, **2008**, 56, 2663-2668	8.4	74
70	Influence of structural imperfection of Σ3 grain boundaries in bulk multicrystalline Si on their electrical activities. *Journal of Applied Physics*, **2007**, 101, 063509	2.5	16
69	Effect of the compositional distribution on the photovoltaic power conversion of SiGe solar cells. *Solar Energy Materials and Solar Cells*, **2007**, 91, 123-128	6.4	14
68	Formation mechanism of parallel twins related to Si-facetted dendrite growth. *Scripta Materialia*, **2007**, 57, 81-84	5.6	68

67	Improvement in the conversion efficiency of single-junction SiGe solar cells by intentional introduction of the compositional distribution. *Journal of Applied Physics*, **2007**, 101, 054504	2.5	5
66	Modification of local structures in multicrystals revealed by spatially resolved x-ray rocking curve analysis. *Journal of Applied Physics*, **2007**, 102, 103504	2.5	12
65	Modification of Local Structure and Its Influence on Electrical Activity of Near (310) Σ5 Grain Boundary in Bulk Silicon. *Materials Transactions*, **2007**, 48, 143-147	1.3	17
64	One-dimensionally curved Si and Ge single crystal wafers prepared by hot-pressing: potential performance for optical components for X-ray diffraction. *Journal of Physics: Conference Series*, **2007**, 83, 012030	0.3	1
63	Realization of Bulk Multicrystalline Silicon with Controlled Grain Boundaries by Utilizing Spontaneous Modification of Grain Boundary Configuration. *Japanese Journal of Applied Physics*, **2006**, 45, 1734-1737	1.4	12
62	High-Efficiency Concave and Conventional Solar Cell Integration System Using Focused Reflected Light. *Japanese Journal of Applied Physics*, **2006**, 45, 1664-1667	1.4	3
61	Suppression of structural imperfection in strained Si by utilizing SiGe bulk substrate. *Applied Physics Letters*, **2006**, 88, 221912	3.4	4
60	??????????????????. *Materia Japan*, **2006**, 45, 720-724	0.1	
59	Si wafers having one- and two-dimensionally curved (111) planes examined by X-ray diffraction. *Journal of Applied Crystallography*, **2006**, 39, 443-445	3.8	7
58	Growth of structure-controlled polycrystalline silicon ingots for solar cells by casting. *Acta Materialia*, **2006**, 54, 3191-3197	8.4	143
57	Directional growth method to obtain high quality polycrystalline silicon from its melt. *Journal of Crystal Growth*, **2006**, 292, 282-285	1.6	90
56	Intermixing of Ge and Si during exposure of GeH4 on Si. *Thin Solid Films*, **2006**, 508, 163-165	2.2	3
55	Control of compound forming reaction at the interface between SnZn solder and Cu substrate. *Journal of Alloys and Compounds*, **2005**, 392, 200-205	5.7	47
54	Growth of InGaAs and SiGe homogeneous bulk crystals which have complete miscibility in the phase diagrams. *International Journal of Materials and Product Technology*, **2005**, 22, 185	1	5
53	Effects of vicinal steps on the island growth and orientation of epitaxially grown perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. *Journal of Crystal Growth*, **2005**, 273, 594-602	1.6	9
52	Growth and properties of SiGe multicrystals with microscopic compositional distribution and their applications for high-efficiency solar cells. *Journal of Crystal Growth*, **2005**, 275, e455-e460	1.6	6
51	Growth of SiGe-on-insulator and its application as a substrate for epitaxy of strained-Si layer. *Journal of Crystal Growth*, **2005**, 275, e1203-e1207	1.6	3
50	A simple approach to determine preferential growth orientation using multiple seed crystals with random orientations and its utilization for seed optimization to restrain polycrystallization of SiGe bulk crystal. *Journal of Crystal Growth*, **2005**, 276, 393-400	1.6	15

49	Structural properties of directionally grown polycrystalline SiGe for solar cells. *Journal of Crystal Growth*, **2005**, 275, 467-473	1.6	13
48	Growth of multicrystalline Si with controlled grain boundary configuration by the floating zone technique. *Journal of Crystal Growth*, **2005**, 280, 419-424	1.6	26
47	Crystal quality of a 6H-SiC layer grown over macrodefects by liquid-phase epitaxy: a Raman spectroscopic study. *Thin Solid Films*, **2005**, 476, 206-209	2.2	23
46	Solar cell system using a polished concave Si-crystal mirror. *Solar Energy Materials and Solar Cells*, **2005**, 88, 323-329	6.4	5
45	Hemisphere-shaped silicon crystal wafers obtained by plastic deformation and preparation of their solar cells. *Journal of Electronic Materials*, **2005**, 34, 1047-1052	1.9	6
44	Analysis of the Dark-Current Density in Solar Cells Based on Multicrystalline SiGe. *Japanese Journal of Applied Physics*, **2005**, 44, 8019-8022	1.4	2
43	Floating Zone Growth of Si Bicrystals Using Seed Crystals with Artificially Designed Grain Boundary Configuration. *Japanese Journal of Applied Physics*, **2005**, 44, L778-L780	1.4	5
42	On the Origin of Improved Conversion Efficiency of Solar Cells Based on SiGe with Compositional Distribution. *Japanese Journal of Applied Physics*, **2005**, 44, 857-860	1.4	5
41	Influence of growth temperature on minority-carrier lifetime of Si layer grown by liquid phase epitaxy using Ga solvent. *Journal of Applied Physics*, **2005**, 98, 073708	2.5	1
40	Liquid Phase Epitaxial Growth of Si Layers on Si Thin Substrates from Si Pure Melts under Near-Equilibrium Conditions. *Japanese Journal of Applied Physics*, **2005**, 44, 5092-5095	1.4	5
39	Ge composition dependence of properties of solar cells based on multicrystalline SiGe with microscopic compositional distribution. *Journal of Applied Physics*, **2004**, 96, 1238-1241	2.5	28
38	Effects of spacer thickness on quantum efficiency of the solar cells with embedded Ge islands in the intrinsic layer. *Applied Physics Letters*, **2004**, 84, 2802-2804	3.4	17
37	Wave-shaped Si crystal wafers obtained by plastic deformation and preparation of their solar cells. *Applied Physics Letters*, **2004**, 85, 5896-5898	3.4	14
36	Rational development of new materials--putting the cart before the horse?. *Nature Materials*, **2004**, 3, 838	27	46
35	Fabrication of solar cell with stacked Ge islands for enhanced absorption in the infrared regime. *Thin Solid Films*, **2004**, 451-452, 604-607	2.2	6
34	Epitaxial relation and island growth of perylene-3.4.9.10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. *Journal of Crystal Growth*, **2004**, 262, 196-201	1.6	20
33	Phase diagram of growth mode for the SiGe/Si heterostructure system with misfit dislocations. *Journal of Crystal Growth*, **2004**, 260, 372-383	1.6	12
32	In situ observation of elementary growth steps on the surface of protein crystals by laser confocal microscopy. *Journal of Crystal Growth*, **2004**, 262, 536-542	1.6	89

31	In-situ observations of melt growth behavior of polycrystalline silicon. *Journal of Crystal Growth*, **2004**, 262, 124-129	1.6	59
30	Effects of growth temperature on the surface morphology of silicon thin films on (111) silicon monocrystalline substrate by liquid phase epitaxy. *Journal of Crystal Growth*, **2004**, 266, 467-474	1.6	6
29	Grain growth behaviors of polycrystalline silicon during melt growth processes. *Journal of Crystal Growth*, **2004**, 266, 441-448	1.6	89
28	Fabrication of SiGe-on-insulator by rapid thermal annealing of Ge on Si-on-insulator substrate. *Applied Surface Science*, **2004**, 224, 95-98	6.7	10
27	On the origin of strain fluctuation in strained-Si grown on SiGe-on-insulator and SiGe virtual substrates. *Applied Physics Letters*, **2004**, 85, 1335-1337	3.4	19
26	Molten metal flux growth and properties of CrSi2. *Journal of Alloys and Compounds*, **2004**, 383, 319-321	5.7	9
25	Fabrication of SiGe-on-Insulator through Thermal Diffusion of Ge on Si-on-Insulator Substrate. *Japanese Journal of Applied Physics*, **2003**, 42, L232-L234	1.4	8
24	High-Temperature Solution Growth and Characterization of Chromium Disilicide. *Japanese Journal of Applied Physics*, **2003**, 42, 7292-7293	1.4	2
23	Growth of SiGe bulk crystals with uniform composition by utilizing feedback control system of the crystal–melt interface position for precise control of the growth temperature. *Journal of Crystal Growth*, **2003**, 250, 298-304	1.6	27
22	Effects of high pressure on the growth kinetics of orthorhombic lysozyme crystals. *Journal of Crystal Growth*, **2003**, 254, 188-195	1.6	19
21	Stacked Ge islands for photovoltaic applications. *Science and Technology of Advanced Materials*, **2003**, 4, 367-370	7.1	10
20	Enhanced quantum efficiency of solar cells with self-assembled Ge dots stacked in multilayer structure. *Applied Physics Letters*, **2003**, 83, 1258-1260	3.4	86
19	High-Quality Crystalline Silicon Layer Grown by Liquid Phase Epitaxy Method at Low Growth Temperature. *Japanese Journal of Applied Physics*, **2003**, 42, L217-L219	1.4	6
18	Influence of the elastic strain on the band structure of ellipsoidal SiGe coherently embedded in the Si matrix. *Journal of Applied Physics*, **2003**, 94, 916-920	2.5	18
17	Fabrication of SiGe bulk crystals with uniform composition as substrates for Si-based heterostructures. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology* , **2002**, 89, 364-367	3.1	4
16	Measurement of intrinsic diffusion coefficients of Al and Ni in Ni3Al using Ni/NiAl diffusion couples. *Acta Materialia*, **2002**, 50, 1571-1579	8.4	85
15	Melt growth of multicrystalline SiGe with large compositional distribution for new solar cell applications. *Solar Energy Materials and Solar Cells*, **2002**, 72, 93-100	6.4	15
14	In situ observations of crystal growth behavior of silicon melt. *Journal of Crystal Growth*, **2002**, 243, 275-282	1.8	64

13	Growth and properties of SiGe multicrystals with microscopic compositional distribution for high-efficiency solar cells. *Solar Energy Materials and Solar Cells*, **2002**, 73, 305-320	6.4	15
12	In situ observation of the Marangoni convection in a NaCl aqueous solutions under microgravity. *Journal of Crystal Growth*, **2002**, 234, 516-522	1.6	6
11	In-situ monitoring system of the position and temperature at the crystal□olution interface. *Journal of Crystal Growth*, **2002**, 236, 125-131	1.6	12
10	Compositional variation in Si-rich SiGe single crystals grown by multi-component zone melting method using Si seed and source crystals. *Journal of Crystal Growth*, **2002**, 240, 373-381	1.6	32
9	New method for measurement of interdiffusion coefficient in high temperature solutions based on Fick's first law. *Journal of Crystal Growth*, **2002**, 241, 387-394	1.6	13
8	Simultaneous in situ measurement of solute and temperature distributions in the alloy solutions. *Journal of Crystal Growth*, **2002**, 242, 313-320	1.6	6
7	Strain distribution of Si thin film grown on multicrystalline-SiGe with microscopic compositional distribution. *Journal of Applied Physics*, **2002**, 92, 7098-7101	2.5	2
6	Control of Macroscopic Absorption Coefficient of Multicrystalline SiGe by Microscopic Compositional Distribution. *Japanese Journal of Applied Physics*, **2002**, 41, L37-L39	1.4	7
5	Evidence of the Presence of Built-in Strain in Multicrystalline SiGe with Large Compositional Distribution. *Japanese Journal of Applied Physics*, **2002**, 41, 4462-4465	1.4	8
4	Evaluation of the diffusion coefficients in liquid GaGe binary alloys using a novel method based on Fick□ first law. *Journal of Non-Crystalline Solids*, **2002**, 312-314, 196-202	3.9	3
3	Growth of SiGe bulk crystal with uniform composition by directly controlling the growth temperature at the crystal□melt interface using in situ monitoring system. *Journal of Crystal Growth*, **2001**, 224, 204-211	1.6	46
2	Physical model for the evaluation of solid□quid interfacial tension in silicon. *Journal of Applied Physics*, **2001**, 90, 750-755	2.5	16
1	Interfacial observations of Ni/Ni3Si and Ni/Ni3Ga diffusion couples. *Philosophical Magazine Letters*, **1997**, 75, 149-154	1	5